

JEIDA Ver.4.2/PCMCIA Rel.2.1 SRAM Card PRODUCT SPECIFICATION Rev.1.2

Memory size: 64 Kbyte
128 Kbyte
256 Kbyte
512 Kbyte
1 Mbyte
2 Mbyte
4 Mbyte

Model #: BN-064HSR(C)
BN-128HSR(C)
BN-256HSR(C)
BN-512HSR(C)
BN-01MHSR(C)
BN-02MHSR(C)
BN-04MHSR(C)

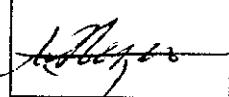
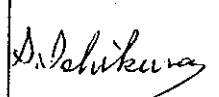
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1. Scope

This products specification relates to the Panasonic SRAM Card BN-HSR series. This SRAM Card conforms to updated Release 2.1 of PC Card standard specification which has been studied by Personal Computer Memory Card International Association (PCMCIA).

2. Products Model

Model #	Common Memory		Attribute Memory		Battery	
	Configuration (Word × bit)	Size (byte)	Configuration	Size(byte)	Main Battery	Sub Battery
BN-064HSR	64K × 8 / 32K × 16	64K	FF Output	No Memory	CR2025 Lithum Battery	Rechargable Battery
BN-128HSR	128K × 8 / 64K × 16	128K				
BN-256HSR	256K × 8 / 128K × 16	256K				
BN-512HSR	512K × 8 / 256K × 16	512K				
BN-01MHSR	1M × 8 / 512K × 16	1M				
BN-02MHSR	2M × 8 / 1M × 16	2M				
BN-04MHSR	4M × 8 / 2M × 16	4M				
BN-064HSRC	64K × 8 / 32K × 16	64K	2K × 8	2K		
BN-128HSRC	128K × 8 / 64K × 16	128K				
BN-256HSRC	256K × 8 / 128K × 16	256K				
BN-512HSRC	512K × 8 / 256K × 16	512K				
BN-01MHSRC	1M × 8 / 512K × 16	1M				
BN-02MHSRC	2M × 8 / 1M × 16	2M				
BN-04MHSRC	4M × 8 / 2M × 16	4M				

3. Outline

3.1 Physical Specification

Length	85.6 ± 0.2 mm
Width	54.0 ± 0.1 mm
Thickness	3.3 ± 0.1 mm
Pin counts	68 pins

3.2 Temperature Condition

Parameters	Symbol	Minimum	Maximum	Unit
Operation Temperature	T _{OPT}	0	60	°C
Storage Temperature	T _{STG}	-20	70	°C

4. Pin Assignment

Pin #	Signal	Pin #	Signal	Pin #	Signal	Pin #	Signal
1	GND	18	VPP1	35	GND	52	VPP2
2	D3	19	A16	36	CD1#	53	A22
3	D4	20	A15	37	D11	54	A23
4	D5	21	A12	38	D12	55	A24
5	D6	22	A7	39	D13	56	A25
6	D7	23	A6	40	D14	57	VS2#
7	CE1#	24	A5	41	D15	58	RESET
8	A10	25	A4	42	CE2#	59	WAIT#
9	OE#	26	A3	43	VS1#	60	RFU
10	A11	27	A2	44	RFU	61	REG#
11	A9	28	A1	45	RFU	62	BVD2
12	A8	29	A0	46	A17	63	BVD1
13	A13	30	D0	47	A18	64	D8
14	A14	31	D1	48	A19	65	D9
15	WE#	32	D2	49	A20	66	D10
16	READY	33	WP	50	A21	67	CD2#
17	VCC	34	GND	51	VCC	68	GND

5. Pin Definition

- ◇ A0 - A25 Address input pins; Up to 64Kbyte memory space is supported. A25 is the most significant bit and A0 is the least significant bit. Address input pins exceeding its memory size are not connected in the card and are full-decoded in each memory space.
- ◇ CE1#, CE2# Card Enable input pins; -CE1 controls even byte and -CE2 does odd byte. Both of them can be accessed on D0 - D7 by combination of A0, CE1# and CE2#.
- ◇ WE# Write Enable input pin; This signal controls the write operation to the card.
- ◇ OE# Output Enable input pin; This signal controls the read operation from the card.
- ◇ REG# Attribute Memory Select input pin; When the low level assertion of this signal, the attribute memory space is enable.
- ◇ READY Ready/ Busy output pin; This signal is NC (Not Connected with any card circuitry).
- ◇ WP Write Protect output pin; WP is at high level during write protection and low level during write enable. This signal reflects write protection status in both common and attribute memory.
- ◇ CD1#, CD2# Card Detection signal output pins; These output GND level and detect insertion or removal of the card. When they are pulled up to VCC at the system side, the insertion or removal of the card can be detected as digital signals through the buffer.
- ◇ VS1#, VS2# Voltage Sense output pins; These signals are prepared to check whether the supported power supply voltage is 3.3 V or 5.0 V. In this card, both are NC indicates 5.0 V only supported. In order to apply this status at the system, the host must have pulled-up resistor from 10 K Ω to 100 K Ω on socket.
- ◇ BVD1, BVD2 Battery Voltage Detection output pins
- ◇ RESET Reset input pin; This signal is NC in this card.
- ◇ WAIT# Wait output pin; This signal is NC in this card.
- ◇ RFU Reserved for Future Use pins; This signal is NC in this card.
- ◇ VCC Power supply pin; In this card, these are for +5V.

- ◇ VPP1, VPP2 Peripheral power supply pins; This signal is NC in this card.
- ◇ GND Ground pins 0V

6. Bias Power Supply Condition

6.1 Absolute Maximum Rating

Parameters	Symbol	Minimum	Maximum	Unit
Power Supply Voltage	V_{CC}	0	6	V
Input Voltage	V_I	-0.5	$V_{CC}+0.5$	V

6.2 Recommended Operation Condition

Parameters	Symbol	Minimum	Typical	Maximum	Unit
Power Supply Voltage	V_{CC}	4.5	5.0	5.5	V
High Level Input Voltage	V_{IH}	2.2		V_{CC}	V
Low Level Input Voltage	V_{IL}	0		0.8	V

7. Truth Table

7.1 Common Memory Read Operation

Function Mode	REG#	CE2#	CE1#	A0	OE#	WE#	D[15:8]	D[7:0]
Standby Mode	X	H	H	X	X	X	Hi-z	Hi-z
Byte Access (8 bit)	H	H	L	L	L	H	Hi-z	Even Byte
	H	H	L	H	L	H	Hi-z	Odd Byte
Word Access (16 bit)	H	L	L	X	L	H	Odd Byte	Even Byte
Odd-Byte-Only Access	H	L	H	X	L	H	Odd Byte	Hi-z

Note X: can be either High level input or Low level input

H: stands for High level input, L: stands for Low level input

Hi-z: stands for High impedance

7.2 Common Memory Write Operation

Function Mode	REG#	CE2#	CE1#	A0	OE#	WE#	D[15:8]	D[7:0]
Standby Mode	X	H	H	X	X	X	Hi-z	Hi-z
Byte Access (8 bit)	H	H	L	L	H	L	Not Valid	Even Byte
	H	H	L	H	H	L	Not Valid	Odd Byte
Word Access (16 bit)	H	L	L	X	H	L	Odd Byte	Even Byte
Odd-Byte-Only Access	H	L	H	X	H	L	Odd Byte	Not Valid

7.3 Attribute Memory Read Operation

Function Mode	REG#	CE2#	CE1#	A0	OE#	WE#	D[15:8]	D[7:0]
Standby Mode	X	H	H	X	X	X	Hi-z	Hi-z
Byte Access (8 bit)	L	H	L	L	L	H	Hi-z	Even Byte
	L	H	L	H	L	H	Hi-z	Not Valid
Word Access (16 bit)	L	L	L	X	L	H	Not Valid	Even Byte
Odd-Byte-Only Access	L	L	H	X	L	H	Not Valid	Hi-z

7.4 Attribute Memory Write Operation

Function Mode	REG#	CE2#	CE1#	A0	OE#	WE#	D[15:8]	D[7:0]
Standby Mode	X	H	H	X	X	X	Hi-z	Hi-z
Byte Access (8 bit)	L	H	L	L	H	L	Not Valid	Even Byte
	L	H	L	H	H	L	Not Valid	Not Valid
Word Access (16 bit)	L	L	L	X	H	L	Not Valid	Even Byte
Odd-Byte-Only Access	L	L	H	X	H	L	Not Valid	Not Valid

8. DC Characteristics

8.1 General Characteristics

V_{CC}=5.0V±10%, Ta=0°C~60°C

Parameter	Symbol	Test Condition	Value			Unit
			Min.	Typ.	Max.	
Active Current	I _{CC1}	V _{CC} =V _{CC} Max., CE1# or CE2#=V _{IL} t _{CR} =200ns, I _{OUT} =0mA			80	mA
	I _{CC2}	V _{CC} =V _{CC} Max., CE1#=CE2#=V _{IL} t _{CR} =200ns, I _{OUT} =0mA			150	mA
Standby Current	I _{SB}	V _{CC} =V _{CC} Max., CE1#=CE2#=V _{IH} Empty charged to Sub Battery			5	mA
		V _{CC} =V _{CC} Max., CE1#=CE2#=V _{IH} Full charged to Sub Battery		100	150	μA
Input Leakage Current	I _{LI}	V _{CC} =V _{CC} Max., V _{IN} =V _{CC} or GND			±10	μA
Output Leakage Current	I _{LO}	V _{CC} =V _{CC} Max., V _{OUT} =V _{CC} or GND			±10	μA
Input Low Voltage	V _{IL}		0		0.8	V
Input High Voltage	V _{IH}		2.2		V _{CC}	V
Output Low Voltage	V _{OL}	I _{OL} =2.0mA			0.4	V
Output High Voltage	V _{OH}	I _{OH} =-1.0mA	3.8			V

8.2 Capacitance (Ta=25°C, f=1.0MHz, not 100% tested)

	Symbol	Maximum Value	Unit
Address signals /Control Signals	C _{IN}	100	pF
Data signals	C _{I/O}	50	pF

8.3 Rewritable Limitation

	Minimum Value	Unit
Attribute Memory (EEPROM)	10,000	Cycle

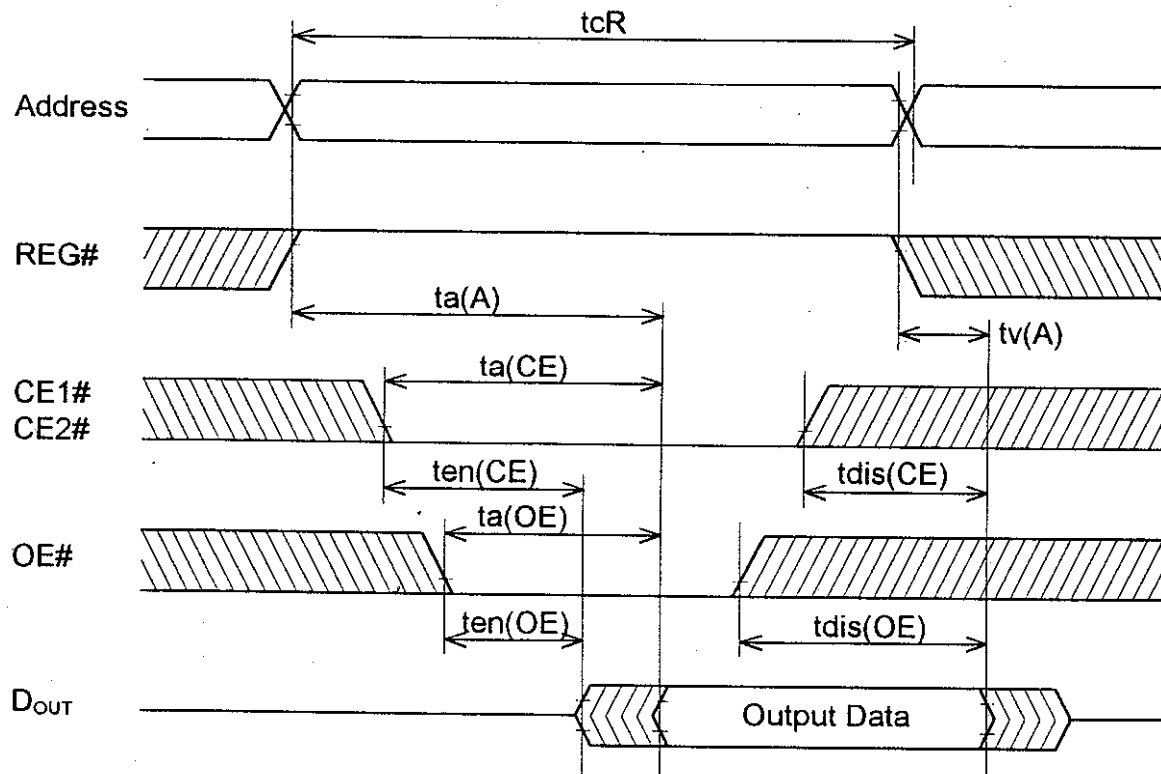
9. AC Characteristics

9.1 Read Cycle Timing (for Common memory and Attribute memory)

 $V_{CC}=5V \pm 10\%$, $T_a=0^\circ\text{C} \sim 60^\circ\text{C}$

Parameter	Symbol	Common Memory		Attribute Memory		Unit
		Min.	Max.	Min.	Max.	
Read Cycle Time	t_{CR}	200		300		ns
Address Access Time	$t_a(A)$		200		300	ns
CE# Access Time	$t_a(CE)$		200		300	ns
OE# Access Time	$t_a(OE)$		100		150	ns
Output Disable Time from CE# Change	$t_{dis}(CE)$		90		100	ns
Output Disable Time from OE# Change	$t_{dis}(OE)$		90		100	ns
Output Enable Time from CE# Change	$t_{en}(CE)$	5		5		ns
Output Enable Time from OE# Change	$t_{en}(OE)$	5		5		ns
Data Valid Time from Address Change	$t_v(A)$	0		0		ns

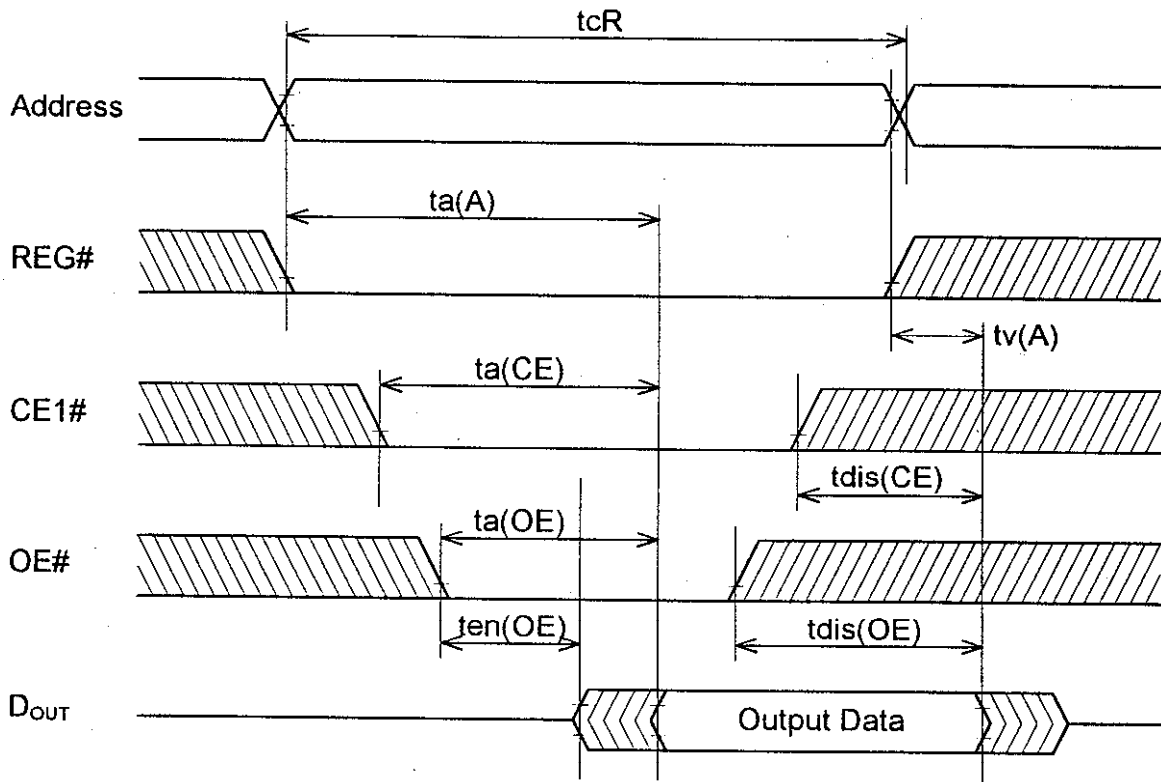
Common Memory Read Cycle Timing Chart



Note:*1 Shaded sections denote area where the input level can be either High or Low.

*2 Output Load: 1TTL+100pF

Attribute Memory Read Cycle Timing Chart



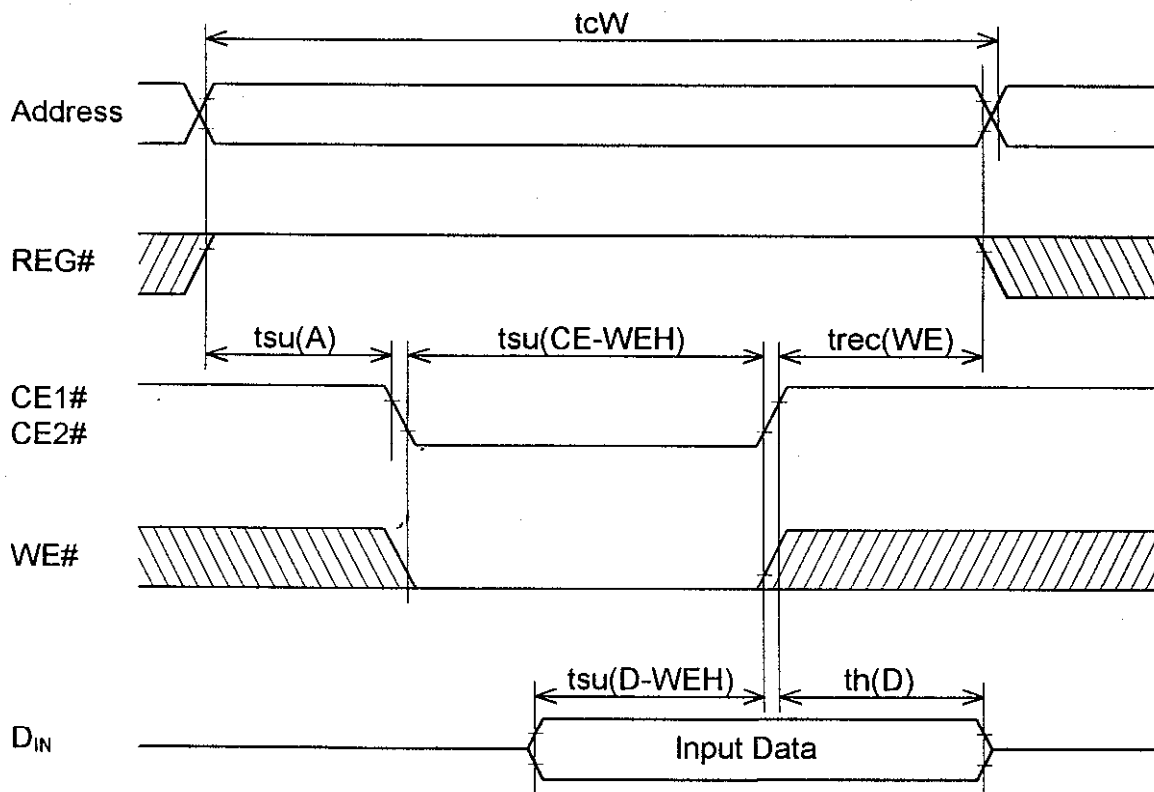
Note: *1 Shaded sections denote area where the input level can be either High or Low.
 *2 Output Load: 1TTL+100pF

9.2 Common memory Write Cycle Timing

 $V_{CC}=5V \pm 10\%$, $T_a=0^\circ\text{C} \sim 60^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Write Cycle Time	t_{cW}	200			ns
Write Pulse Width	$t_w(\text{WE})$	120			ns
Address Set-up Time	$t_{su}(\text{A})$	20			ns
Address Set-up Time from WE# Change	$t_{su}(\text{A-WEH})$	140			ns
CE# Set-up Time from WE# Change	$t_{su}(\text{CE-WEH})$	140			ns
Data Set-up Time from WE# Change	$t_{su}(\text{D})$	60			ns
Data Hold Time	$t_h(\text{D})$	30			ns
Write Recovery Time	$t_{rec}(\text{WE})$	30			ns
Output Disable Time from OE#	$t_{dis}(\text{OE})$			90	ns
Output Disable Time from CE#	$t_{dis}(\text{CE})$			90	ns
Output Enable Time from WE#	$t_{en}(\text{WE})$	5			ns
Output Enable Time from OE#	$t_{en}(\text{OE})$	5			ns
OE# Set-up Time from WE#	$t_{su}(\text{OE-WE})$	10			ns
OE# Hold Time from WE#	$t_h(\text{OE-WE})$	10			ns

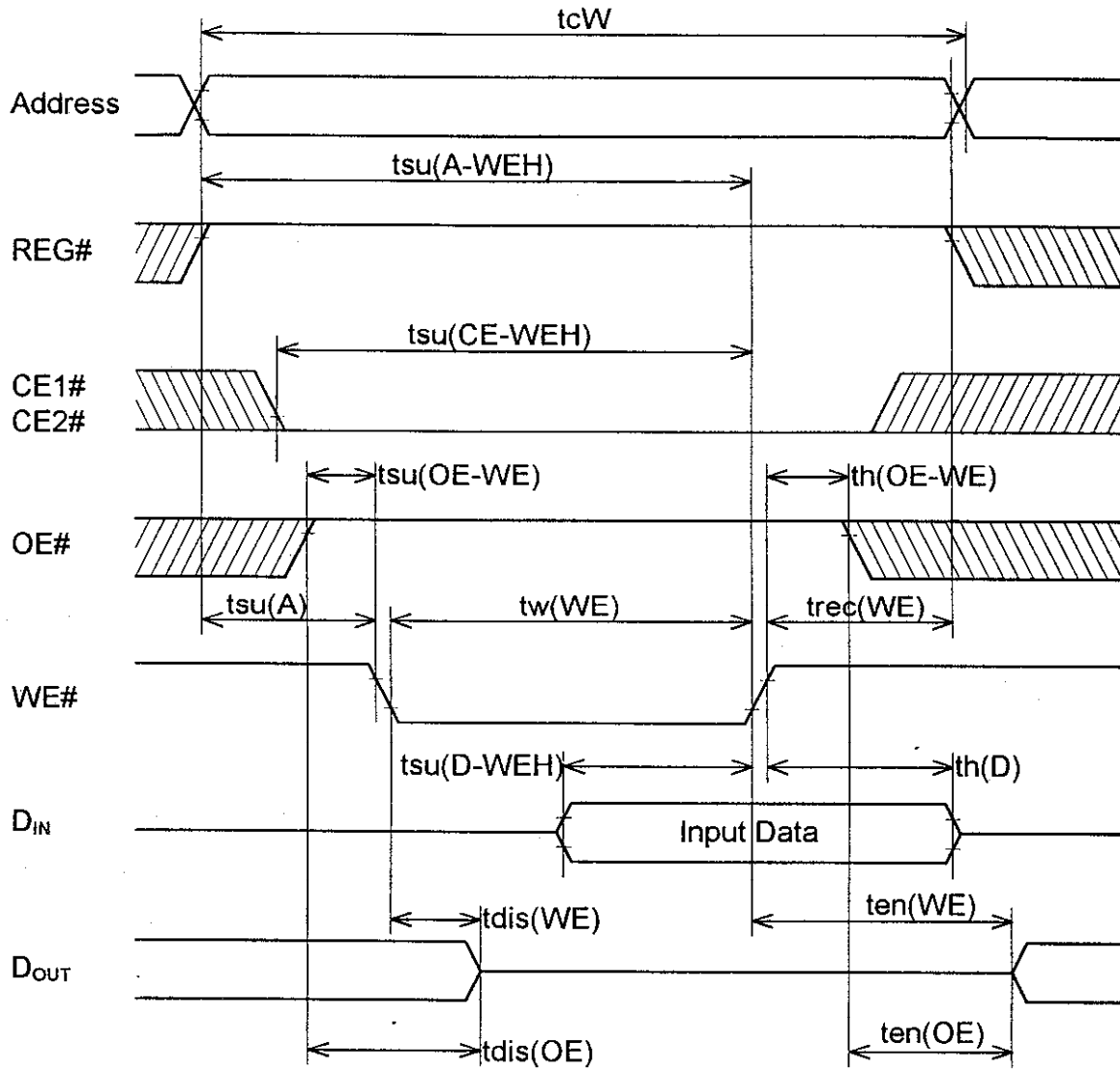
CE# Controlled Common Memory Write Timing Chart



Note: *1 Shaded sections denote areas where the input level can be either High or Low.

*2 When the data I/O signal is in output mode, input signal should not be applied to the card.

WE# Controlled Common Memory Write Timing Chart



Note: *1 Shaded sections denote areas where the input level can be either High or Low.

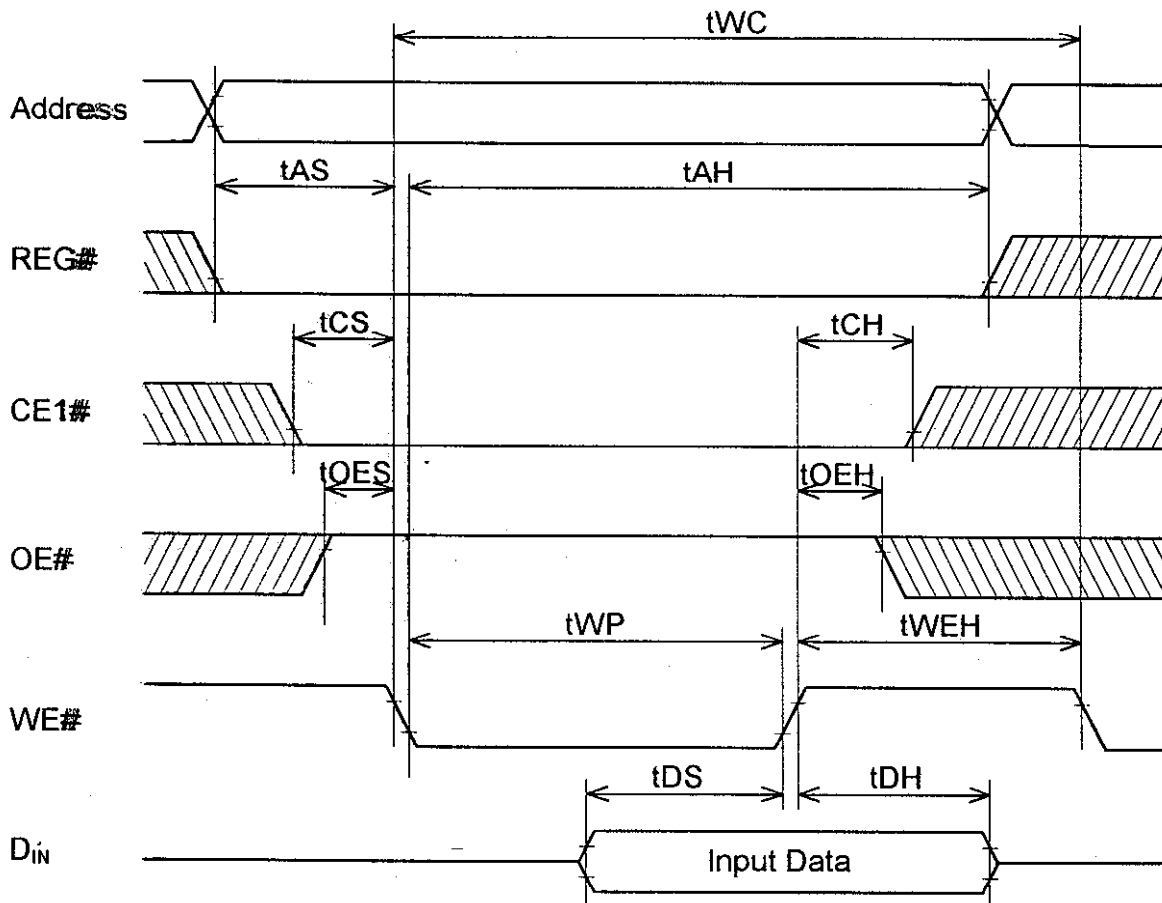
*2 When the data I/O signal is in output mode, input signal should not be applied to the card.

9.3 Attribute Memory Write Timing

 $V_{CC}=5V \pm 10\%$, $T_a=0^{\circ}C-70^{\circ}C$

Parameter	Symbol	Min.	Typ.	Max.	Unit
Write Cycle Time	tWC	1.0			ms
Address Set-up Time	tAS	10			ns
Address Hold Time	tAH	100			ns
CE# Set-up Time	tCS	20			ns
CE# Hold Time	tCH	20			ns
CE# Write Pulse Width	tCW	100			ns
OE# Set-up Time	tOES	15			ns
OE# Hold Time	tOEH	30			ns
WE# Write Pulse Width	tWP	100			ns
WE# Write High Pulse Width	tWEH	0.9			ms
CE# Write High Pulse Width	tCEH	0.9			ms
Data Set-up Time	tDS	100			ns
Data Hold Time	tDH	20			ns

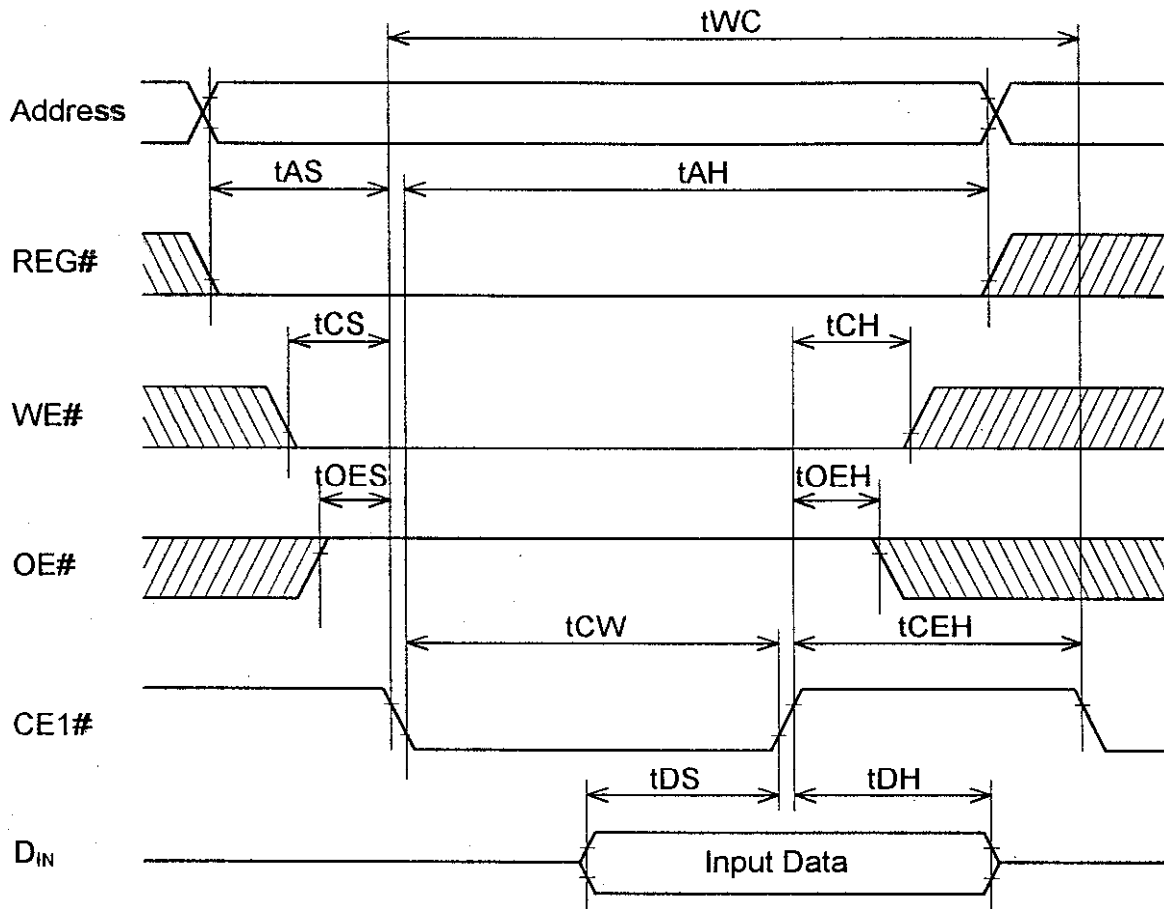
WE# Controlled Attribute Memory Write Timing Chart



Note: *1 Shaded sections denote area where the input level can be either High or Low.

*2 When the data I/O signal is in output mode, input signal should not be applied to the card.

CE# Controlled Attribute Memory Write Timing Chart



Note: *1 Shaded sections denote area where the input level can be either High or Low.

*2 When the data I/O signal is in output mode, input signal should not be applied to the card.

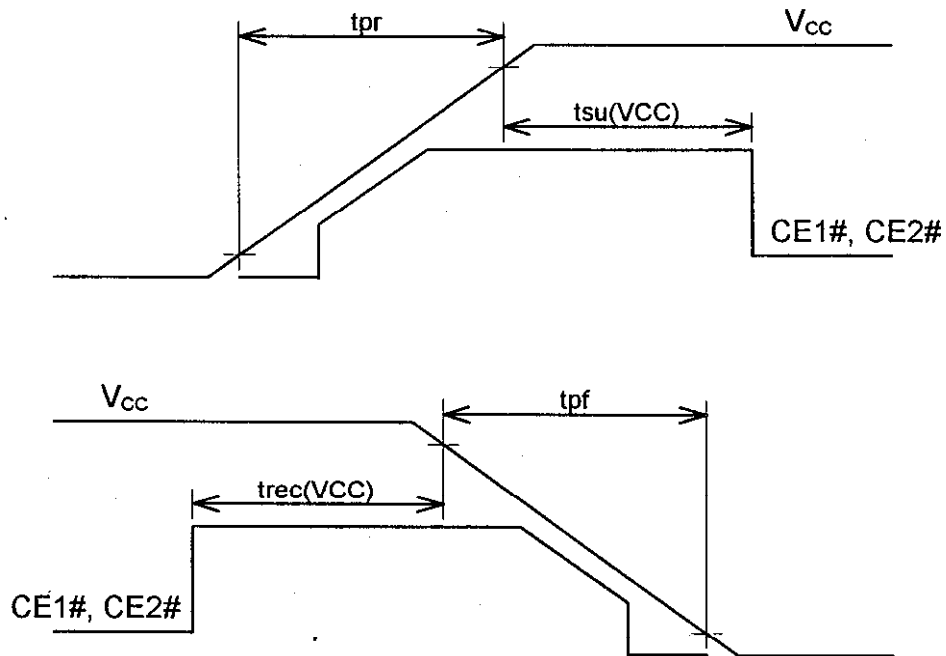
10. Power-up and down Sequence

10.1 Power-up and down Timing

 $V_{CC}=5.0V \pm 10\%$, $T_a=0^{\circ}C \sim 60^{\circ}C$

Parameter	Symbol	Test Condition	Value		Unit
			Min.	Max.	
CE# Set-up Time from V_{CC}	$t_{su}(V_{CC}-CE\#)$		20		ms
CE# Recovery Time from V_{CC}	$t_{rec}(CE\#-V_{CC})$		1.0		μs
VCC Rising Time	t_{pr}	from $0.1V_{CC}$ to $0.9(V_{CC}+5\%)$	0.1	300	ms
VCC Falling Time	t_{pf}	from $0.9(V_{CC}-5\%)$ to $0.1V_{CC}$	3.0	300	ms

Power-up and down Timing

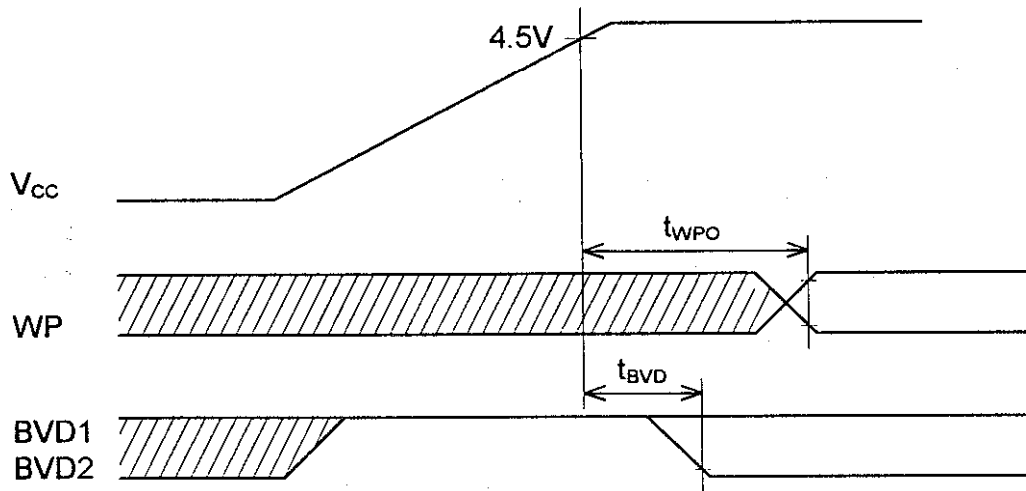


10.2 Status Output Timing

$V_{CC}=5.0V \pm 10\%$, $T_a=0^{\circ}C \sim 60^{\circ}C$

Parameter	Symbol	Test Condition	Value		Unit
			Typ.	Max.	
BVD Output Delay Time	t_{BVD}		10		ms
WP Output Delay Time	t_{WPO}		1.5	2.0	ms

Status Output Timing



11. Electrical Interface

Signal Type	Memory Size	Signal	Electrical Interface
Control Signals		CE1#	Pulled-up 20K Ω to V _{CC}
		CE2#	Pulled-up 20K Ω to V _{CC}
		REG#	Pulled-up 20K Ω to V _{CC}
		OE#	Pulled-up 20K Ω to V _{CC}
		WE#	Pulled-up 20K Ω to V _{CC}
		RESET	NC*1
Address Signals	64KB	A[0:15]	No Register*2
		A[16:25]	NC
	128KB	A[0:15]	No Register
		A16	Pulled-down 100K Ω to GND
	256KB	A[17:25]	NC
		A[0:17]	No Register
	512KB	A[18:25]	NC
		A[0:18]	No Register
	1MB	A[19:25]	NC
		A[0:18]	No Register
		A19	Pulled-down 100K Ω to GND
	2MB	A[20:25]	NC
		A[0:18]	No Register
		A[19:20]	Pulled-down 100K Ω to GND
	4MB	A[21:25]	NC
		A[0:18]	No Register
		A[19:21]	Pulled-down 100K Ω to GND
			A[22:25]
Data Signals		D[0:15]	No Register
Output Signals		BVD1	No Register
		BVD2	No Register
		READY	NC
		WP	No Register
		WAIT#	NC
		CD1#	GND Level
		CD2#	GND Level
Peripheral Power Supply		V _{PP1}	NC
		V _{PP2}	NC

Note *1 NC stands for Not Connected with any circuitry in the card.

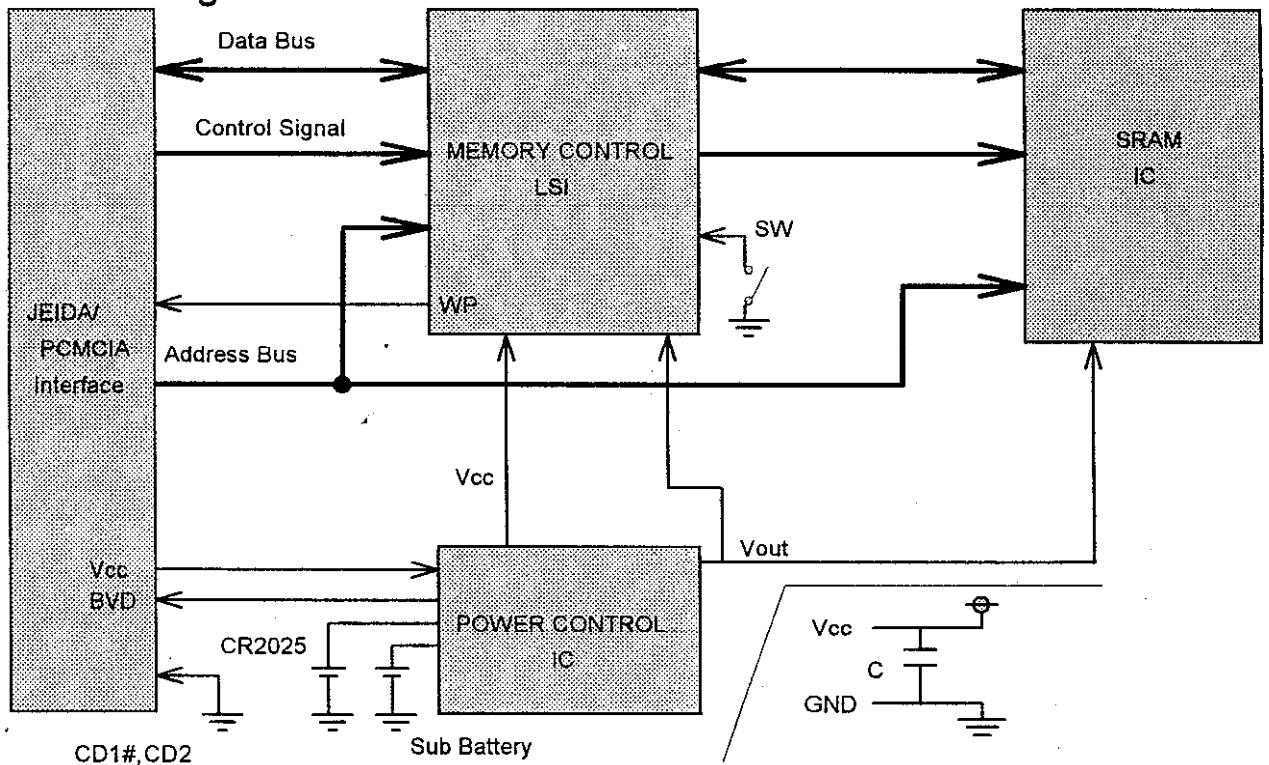
*2 "No Register" means signal is directly connected with circuitry in the card.

12. Card Information Structure

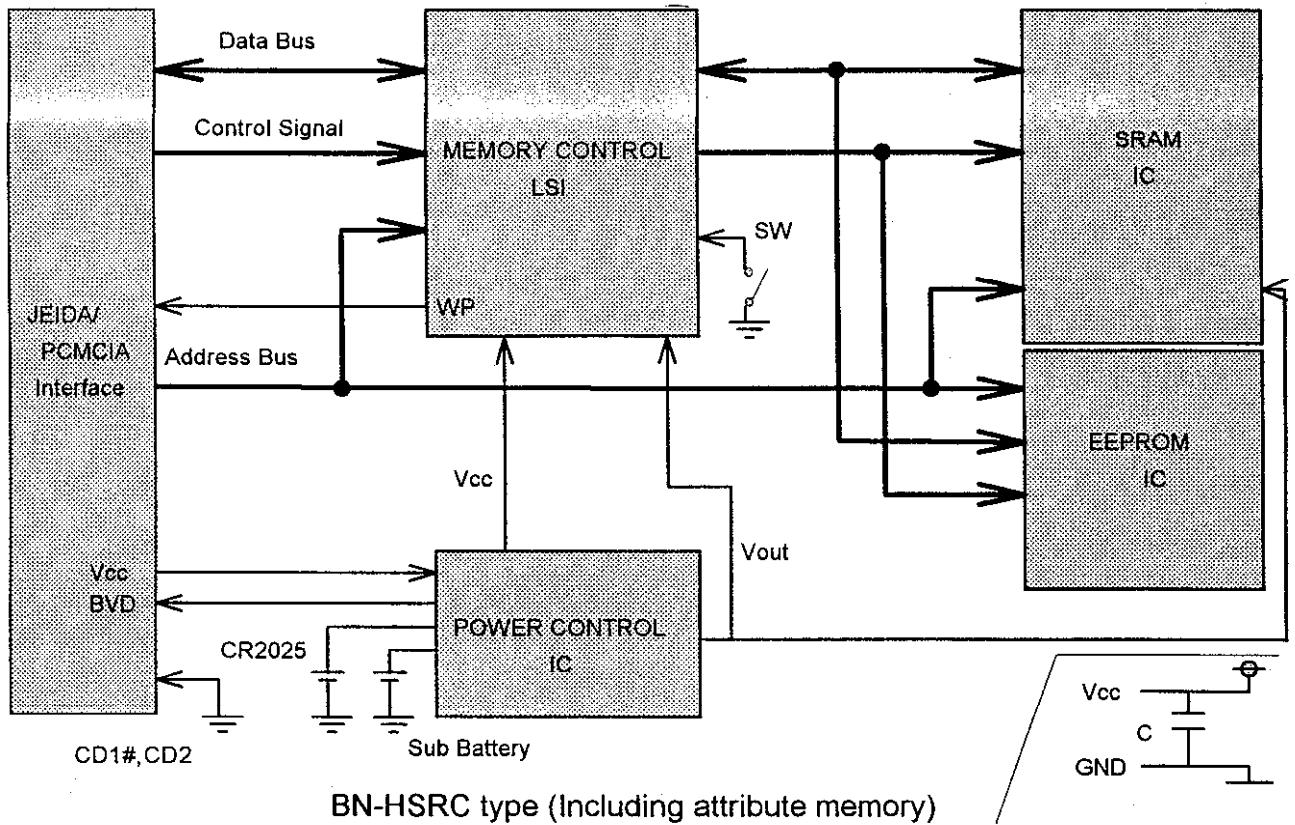
BN-HSRC type in this series includes some Card Information structure (CIS) at the shipment which shares just 6 byte on 2 Kbyte attribute memory plane. This content is as follows. It's possible for user to store favorite CIS by additional writing because of EEPROM device as attribute memory. Please refer to electrical specification considering attribute memory.

Address	Data	Symbol	Description
00h	01h	CISTPL_DEVICE_C	Common Memory Device Information Tuple
02h	03h	TPL_LINK	
04h	62h	DTYPE_SRAM, DSPEED_200NS	SRAM, 200ns, WP flag Available
06h	0Bh		64KB
	1Bh		128KB
	3Bh		256KB
	7Bh		512KB
	FBh		1MB
	1Dh		2MB
	3Dh		4MB
08h	FFh		End of Common Memory Device Info Tuple
0Ah	FFh	CISTPL_END	End of Tuple List

13. Block Diagram



BN-HSR type (Not including attribute memory)



14. Battery

14.1 Data Retention

Memory Size	Memory Back-up time
	Ta=25°C
64Kbyte	5 years
128Kbyte	5 years
256Kbyte	5 years
512Kbyte	5 years
1Mbyte	4 years
2Mbyte	2 years
4Mbyte	1 year

Note: *1 CR2025 battery produced by Panasonic should be used for main back-up battery of this card.

*2 These values are estimated back-up time when Panasonic CR2025 is used for back-up.

14.2 Battery Voltage Detection

BVD1(#63)	BVD2(#62)	Definition
H	H	Battery Operational
H	L	Battery Operational, but battery should be replaced.
L	H	Not available data retention, battery should be replaced.
L	L	Not available data retention, battery should be replaced.

Note: "H" and "L" in the table indicate High and Low Output Level each other.

14.3 Battery Replacement

This card also includes Sub Battery which becomes back-up battery during replacement of main battery CR2025. It's possible to replace new CR2025 within approximately 1 hour without external power supply from V_{CC} .